

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 01-264218
(43)Date of publication of application : 20.10.1989

(51)Int.Cl. H01L 21/205
H01L 21/365

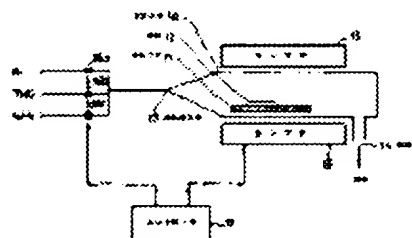
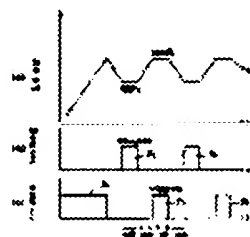
(21)Application number : 63-092926 (71)Applicant : FUJITSU LTD
(22)Date of filing : 15.04.1988 (72)Inventor : MOCHIZUKI KOJI
OTSUKA NOBUYUKI
OZEKI MASASHI

(54) ATOMIC LAYER EPITAXIAL GROWTH

(57)Abstract:

PURPOSE: To realize epitaxial growth with economical atomic weight at high speed and at high throughput by a method wherein a substrate temperature is changed in synchronization with the timing of the supply of a raw material, a gas having a low decomposition temperature is lowered and a gas having a high decomposition temperature is supplied when the substrate temperature is raised.

CONSTITUTION: First, a controller 17 instructs lamp furnaces 15 to execute a heating operation; a temperature of a substrate 12 is raised up to 600° C. During this process, the controller 17 supplies valves 16a and 16c with a pulse P1; these are opened. By this setup, H₂ gas and AsH₃ gas with a high decomposition temperature are supplied to the inside of a reactor 10 via a gas introduction port 13. These gases are supplied in order to protect a substrate 12. Then, after an evacuation the controller 17 stops the heating operation of the lamp furnaces 15 and sets the temperature of the substrate to 400° C. The controller 17 monitors the temperature of the substrate 12 by using a temperature detector such as a thermocouple or the like; when the temperature of the substrate 12 reaches 400° C, a pulse P2 is given to valves 16a and 16b; H₂ gas and TMG having a low decomposition temperature are supplied to the inside of the reactor 10.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]